



OCTAL D-TYPE FLIP FLOP WITH 3 STATE OUTPUT NON INVERTING

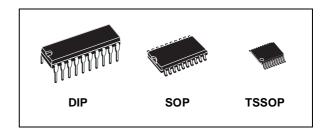
- HIGH SPEED:
 - $f_{MAX} = 90MHz$ (TYP.) at $V_{CC} = 6V$
- LOW POWER DISSIPATION: $I_{CC} = 4\mu A(MAX.)$ at $T_A=25^{\circ}C$
- HIGH NOISE IMMUNITY: V_{NIH} = V_{NIL} = 28 % V_{CC} (MIN.)
- SYMMETRICAL OUTPUT IMPEDANCE: |I_{OH}| = I_{OL} = 6mA (MIN)
- BALANCED PROPAGATION DELAYS: t_{PLH} ≅ t_{PHL}
- WIDE OPERATING VOLTAGE RANGE: V_{CC} (OPR) = 2V to 6V
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 574



The M74HC574 is an high speed CMOS OCTAL D-TYPE FLIP FLOP WITH 3-STATE OUTPUTS INVERTING fabricated with sub-micron silicon gate C²MOS technology.

This 8 bit D-TYPE FLIP FLOP is controlled by a clock input (CK) and an output enable input (OE). On the positive transition of the clock, the Q outputs will be set to the logic state that were setup at the D inputs.

While the $\overline{\text{OE}}$ input is at low level, the eight outputs will be in a normal logic state (high or low logic



ORDER CODES

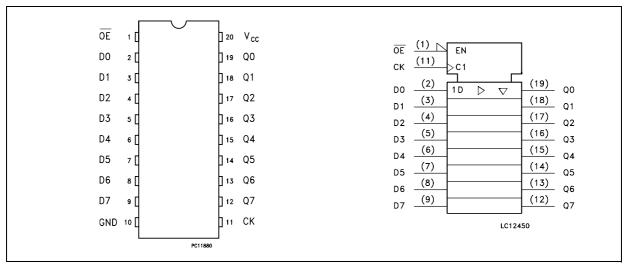
PACKAGE	TUBE	T & R
DIP	M74HC574B1R	
SOP	M74HC574M1R	M74HC574RM13TR
TSSOP		M74HC574TTR

level) and while \overline{OE} is in high level the outputs will be in a high impedance state.

The output control does not affect the internal operation of flip-flops; that is, the old data can be retained or the new data can be entered even while the outputs are off.

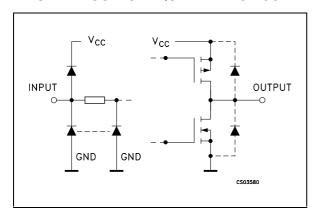
All inputs are equipped with protection circuits against static discharge and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



July 2001 1/11

INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

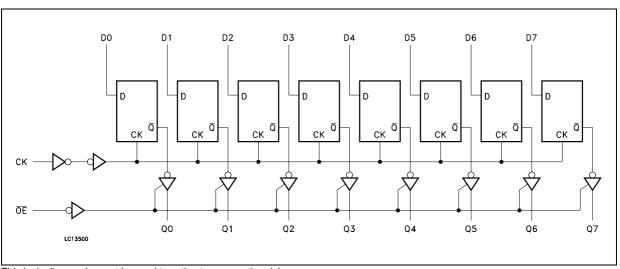
PIN No	SYMBOL	NAME AND FUNCTION
1	OE	3 State Output Enable Input (Active LOW)
2, 3, 4, 5, 6, 7, 8, 9	D0 to D7	Data Inputs
12, 13, 14, 15, 16, 17, 18, 19	Q7 to Q0	3 State Outputs
11	CK	Clock Input (LOW to HIGH, edge triggered)
10	GND	Ground (0V)
20	V _{CC}	Positive Supply Voltage

TRUTH TABLE

	INPUTS						
ŌE	СК	D	Q				
Н	X	Х	Z				
L		X	NO CHANGE				
L		L	L				
L		Н	Н				

X: Don't Care Z: High Impedance

LOGIC DIAGRAM



This logic diagram has not be used to estimate propagation delays

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7	V
V _I	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
V _O	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
Ιο	DC Output Current	± 35	mA
I_{CC} or I_{GND}	DC V _{CC} or Ground Current	± 70	mA
P_{D}	Power Dissipation	500(*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
TL	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied

(*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit	
V _{CC}	Supply Voltage		2 to 6	V
V _I	Input Voltage		0 to V _{CC}	V
V _O	Output Voltage		0 to V _{CC}	V
T _{op}	Operating Temperature		-55 to 125	°C
	Input Rise and Fall Time	$V_{CC} = 2.0V$	0 to 1000	ns
t _r , t _f		V _{CC} = 4.5V	0 to 500	ns
		V _{CC} = 6.0V	0 to 400	ns

DC SPECIFICATIONS

		7	Test Condition	Value							
Symbol	Parameter	v _{cc}		Т	$T_A = 25^{\circ}C$		-40 to 85°C		-55 to 125°C		Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V _{IH}	High Level Input	2.0		1.5			1.5		1.5		
	Voltage	4.5		3.15			3.15		3.15		V
		6.0		4.2			4.2		4.2		
V_{IL}	Low Level Input	2.0				0.5		0.5		0.5	
	Voltage	4.5				1.35		1.35		1.35	V
		6.0				1.8		1.8		1.8	
V _{OH}	High Level Output	2.0	I _O =-20 μA	1.9	2.0		1.9		1.9		
Voltage	4.5	I _O =-20 μA	4.4	4.5		4.4		4.4		V	
	6.0	I _O =-20 μA	5.9	6.0		5.9		5.9			
		4.5	I _O =-6.0 mA	4.18	4.31		4.13		4.10		
		6.0	I _O =-7.8 mA	5.68	5.8		5.63		5.60		
V _{OL}	Low Level Output	2.0	I _O =20 μA		0.0	0.1		0.1		0.1	
	Voltage	4.5	I _O =20 μA		0.0	0.1		0.1		0.1	
		6.0	I _O =20 μA		0.0	0.1		0.1		0.1	V
		4.5	I _O =6.0 mA		0.17	0.26		0.33		0.40	
		6.0	I _O =7.8 mA		0.18	0.26		0.33		0.40	
I _I	Input Leakage Current	6.0	$V_I = V_{CC}$ or GND			± 0.1		± 1		± 1	μΑ
I _{OZ}	High Impedance Output Leakage Current	6.0	$V_I = V_{IH} \text{ or } V_{IL}$ $V_O = V_{CC} \text{ or GND}$			± 0.5		± 5		± 10	μА
I _{CC}	Quiescent Supply Current	6.0	$V_I = V_{CC}$ or GND			4		40		80	μΑ

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ns}$)

		7	est Co	ondition	Value							
Symbol	Parameter	v _{cc}	CL		Т	T _A = 25°C		-40 to	85°C	-55 to	125°C	Unit
		(V)	(pF)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
t _{TLH} t _{THL}	Output Transition	2.0				25	60		75		90	
	Time	4.5	50			7	12		15		18	ns
		6.0				6	10		13		15	
t _{PLH} t _{PHL}	Time	2.0				70	150		190		225	
		4.5	50			20	30		38		45	ns
	(CK - Q)	6.0				15	26		32		38	
		2.0				88	190		240		285	
		4.5	150			25	38		48		57	ns
		6.0				19	32		41		48	
t _{PZL} t _{PZH}	t _{PZL} t _{PZH} High Impedance Output Enable Time	2.0				48	125		155		190	
		4.5	50	$R_L = 1 \text{ K}\Omega$		15	25		31		38	ns
		6.0				12	21		26		32	
		2.0				60	165		205		250	
		4.5	150	$R_L = 1 \text{ K}\Omega$		20	33		41		50	ns
		6.0				16	28		35		43	
t _{PLZ} t _{PHZ}	High Impedance	2.0				34	125		155		190	
	Output Disable	4.5	50	$R_L = 1 \text{ K}\Omega$		17	25		31		38	ns
	Time	6.0				15	21		26		32	
f _{MAX}	Maximum Clock	2.0			6.2	18		5		4.2		
	Frequency	4.5	50		31	75		25		21		MHz
		6.0			37	90		30		25		
t _{W(L)}	Minimum Pulse	2.0				15	75		95		110	
t _{W(H)}	Width	4.5	50			6	15		19		22	ns
	(CLOCK)	6.0				6	13		16		19	
t _s	Minimum Set-up	2.0				25	75		95		110	
	Time	4.5	50			6	15		19		22	ns
		6.0				4	13		16		19	
t _h	Minimum Hold	2.0					0		0		0	
	Time 4.5 50 6.0	4.5	50				0		0		0	ns
					0		0		0			

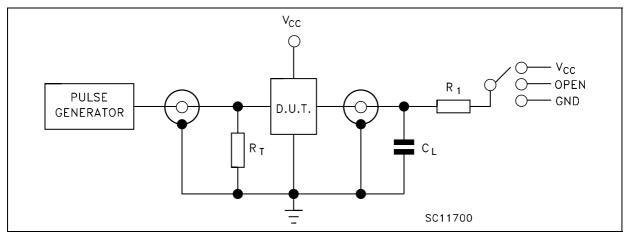
CAPACITIVE CHARACTERISTICS

		Test Condition		Value								
Symbol Parameter	Parameter	V _{CC}		T _A = 25°C			-40 to 85°C		-55 to 125°C		Unit	
	(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.			
C _{IN}	Input Capacitance					5	10		10		10	pF
C _{OUT}	Output Capacitance					10						pF
C _{PD}	Power Dissipation Capacitance (note 1)					54						pF

¹⁾ C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}$



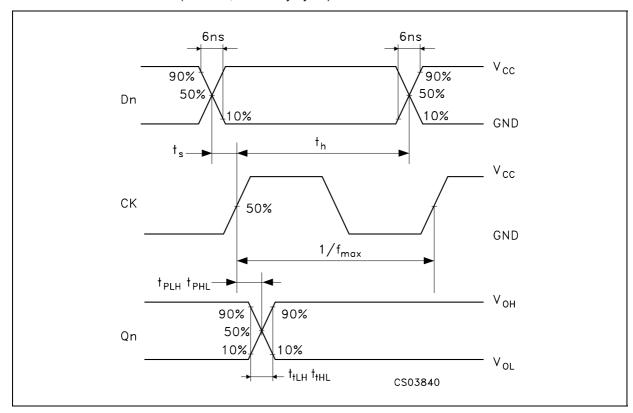
TEST CIRCUIT



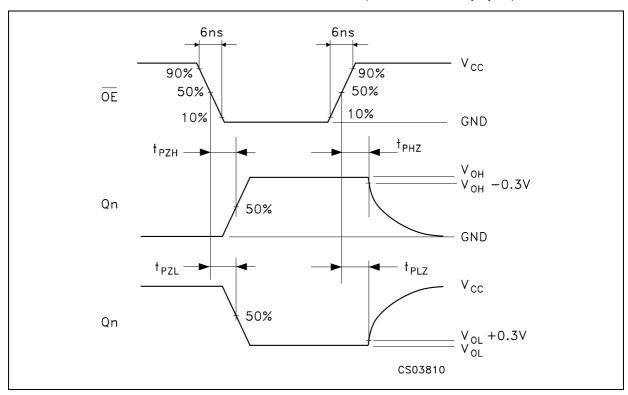
TEST	SWITCH
t _{PLH} , t _{PHL}	Open
t _{PZL} , t _{PLZ}	V _{CC}
t _{PZH} , t _{PHZ}	GND

 C_L = 50pF/150pF or equivalent (includes jig and probe capacitance) R_1 = 1K Ω or equivalent R_T = Z_{OUT} of pulse generator (typically 50 Ω)

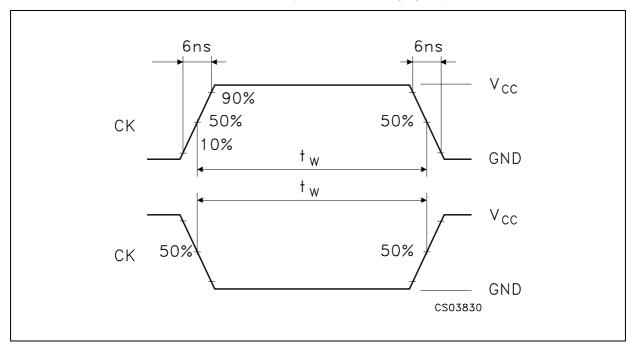
WAVEFORM 1: CK TO Qn PROPAGATION DELAYS, CK MAXIMUM FREQUENCY, Dn TO CK **SETUP AND HOLD TIMES** (f=1MHz; 50% duty cycle)







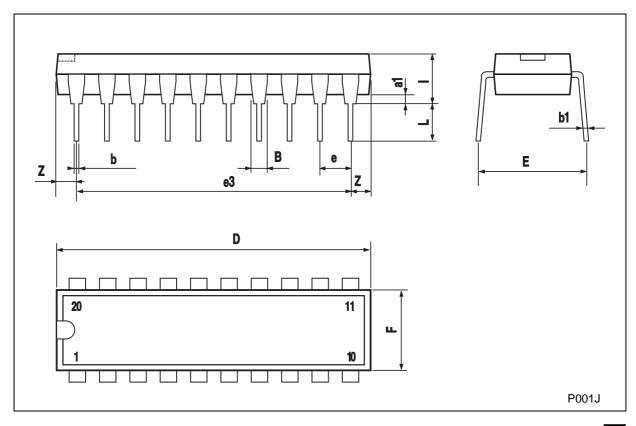
WAVEFORM 3: CK MINIMUM PULSE WIDTH (f=1MHz; 50% duty cycle)



57

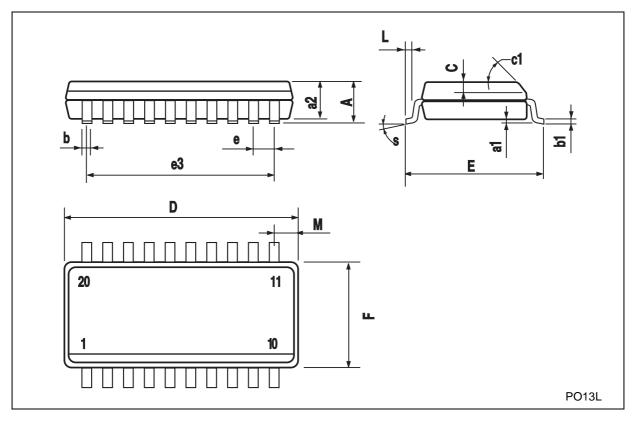
Plastic DIP-20 (0.25) MECHANICAL DATA

DIM		mm.				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
a1	0.254			0.010		
В	1.39		1.65	0.055		0.065
b		0.45			0.018	
b1		0.25			0.010	
D			25.4			1.000
E		8.5			0.335	
е		2.54			0.100	
e3		22.86			0.900	
F			7.1			0.280
I			3.93			0.155
L		3.3			0.130	
Z			1.34			0.053



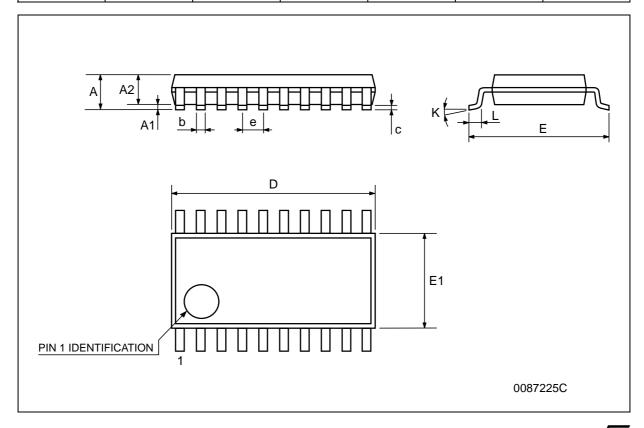
SO-20 MECHANICAL DATA

DIM		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α			2.65			0.104
a1	0.1		0.2	0.004		0.008
a2			2.45			0.096
b	0.35		0.49	0.014		0.019
b1	0.23		0.32	0.009		0.012
С		0.5			0.020	
c1			45°	(typ.)		
D	12.60		13.00	0.496		0.512
Е	10.00		10.65	0.393		0.419
е		1.27			0.050	
e3		11.43			0.450	
F	7.40		7.60	0.291		0.300
L	0.50		1.27	0.020		0.050
М			0.75			0.029
S		ı	8° (r	max.)	ı	



TSSOP20 MECHANICAL DATA

DIM		mm.		inch			
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
А			1.2			0.047	
A1	0.05		0.15	0.002	0.004	0.006	
A2	0.8	1	1.05	0.031	0.039	0.041	
b	0.19		0.30	0.007		0.012	
С	0.09		0.20	0.004		0.0089	
D	6.4	6.5	6.6	0.252	0.256	0.260	
E	6.2	6.4	6.6	0.244	0.252	0.260	
E1	4.3	4.4	4.48	0.169	0.173	0.176	
е		0.65 BSC			0.0256 BSC		
К	0°		8°	0°		8°	
L	0.45	0.60	0.75	0.018	0.024	0.030	



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